

FIG. 1

Polyvinyl phenol resin

Novolak resin

Transmittance

5 Wavelength

FIG. 11

Microprocessor

10 FIG. 13

Microprocessor IP

FIG. 15

100: Pattern of IP mask is written and developed to form
15 resist pattern.

101: IP resist master mask is completed.

101: IP-master mask

102: Product mask is exposed and developed.

103: Whether or not pattern transfer regions are dislocated
20 from each other?

reproduction

104: Metal film of product mask is etched.

105: Product mask is completed.

25 FIG. 18

100: Pattern of IP mask is written and developed to form
resist pattern.

101: IP resist master mask is completed.

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101: IP-master mask

102a: Product mask is exposed and developed.

103a: Whether or not pattern transfer regions are dislocated
from each other?

5 reproduction

105a: Product resist mask is completed.

FIG. 20

100a: Pattern of IP mask is written and developed to form
10 resist pattern.

100b: Pattern of IP mask is written and developed to form
resist pattern.

101a: IP resist master mask is completed.

101b: Metal film of IP mask is etched.

15 101: IP-master mask

101c: IP master mask is completed.

101c: IP master mask

102a: Product mask is exposed and developed.

103a: Whether or not pattern transfer regions are dislocated
20 from each other?

reproduction

105a: Product resist mask is completed.

FIG. 24

25 200: IP master mask

201: Intermediate master mask is exposed and developed.

202: Whether or not pattern transfer regions are dislocated
from each other?

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reproduction

203: Metal mask of intermediate master mask is etched.

204: Intermediate master mask is completed.

205: IP master mask is exposed and developed.

5 206: Whether or not pattern transfer regions are dislocated
from each other?

reproduction

207: Product partial resist mask is completed.

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10 FIG. 27

Old product mask

300: Resist is removed and washed.

301: Intermediate master mask is restored.

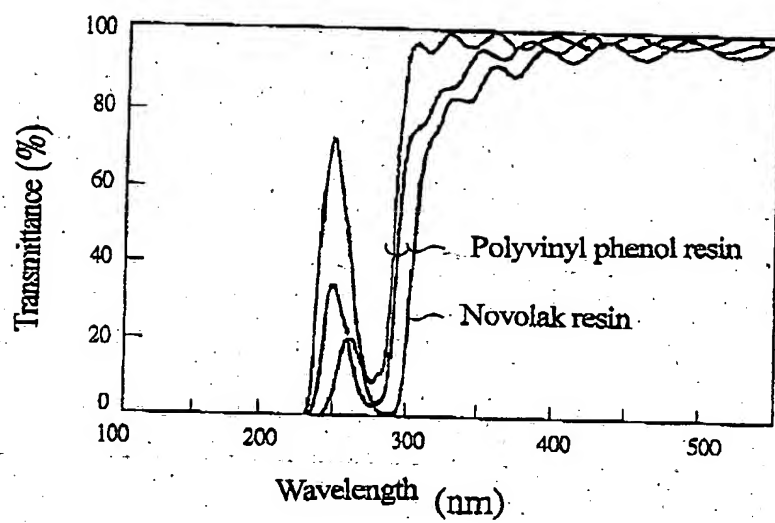
205: IP master mask is exposed and developed.

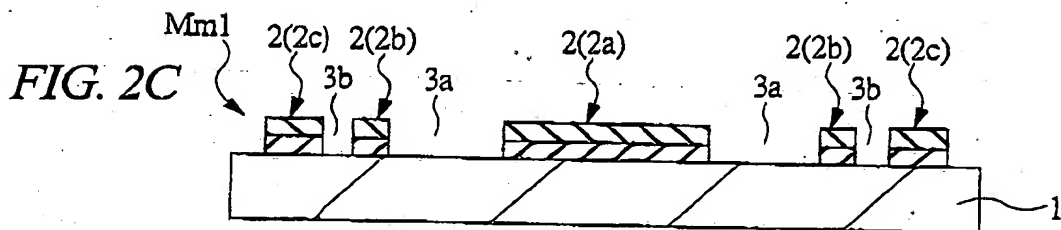
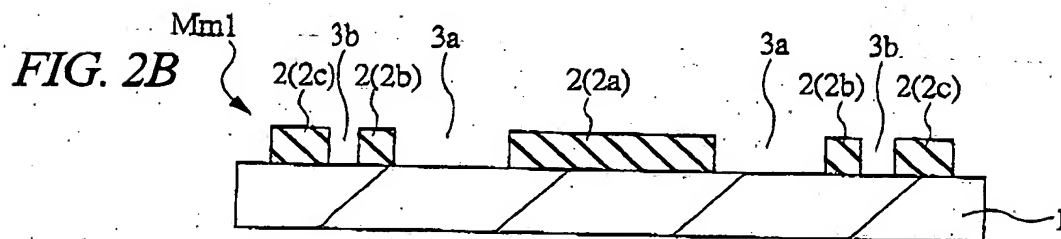
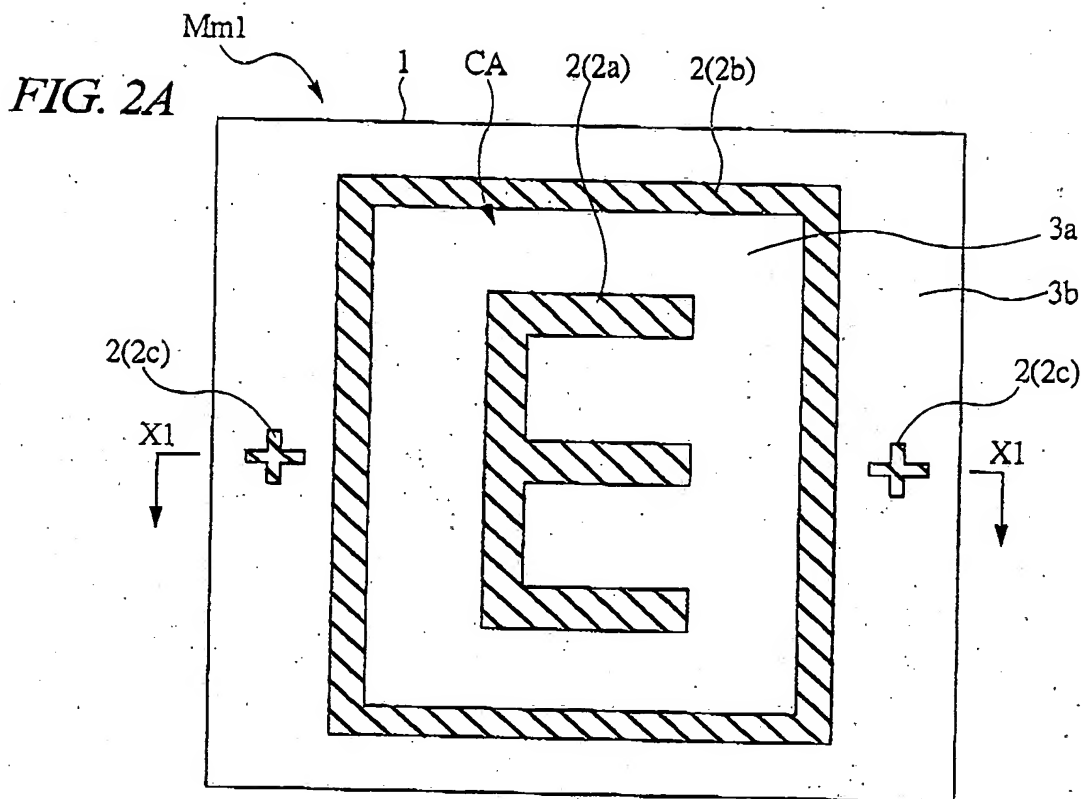
15 206: Whether or not pattern transfer regions are dislocated
from each other?

reproduction

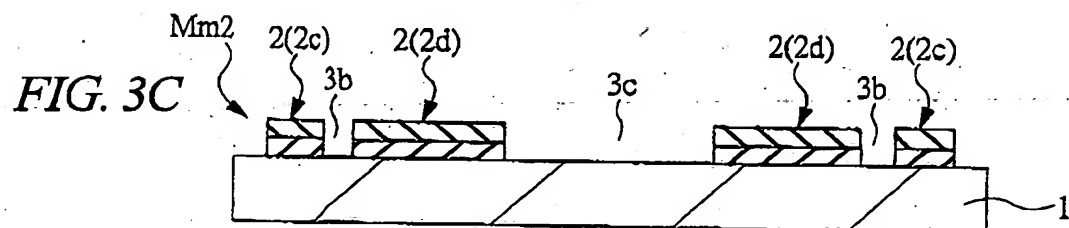
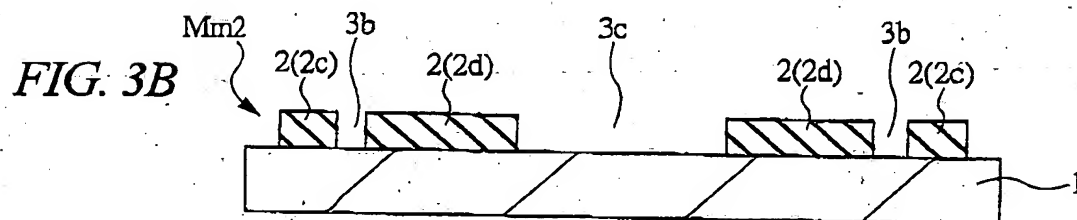
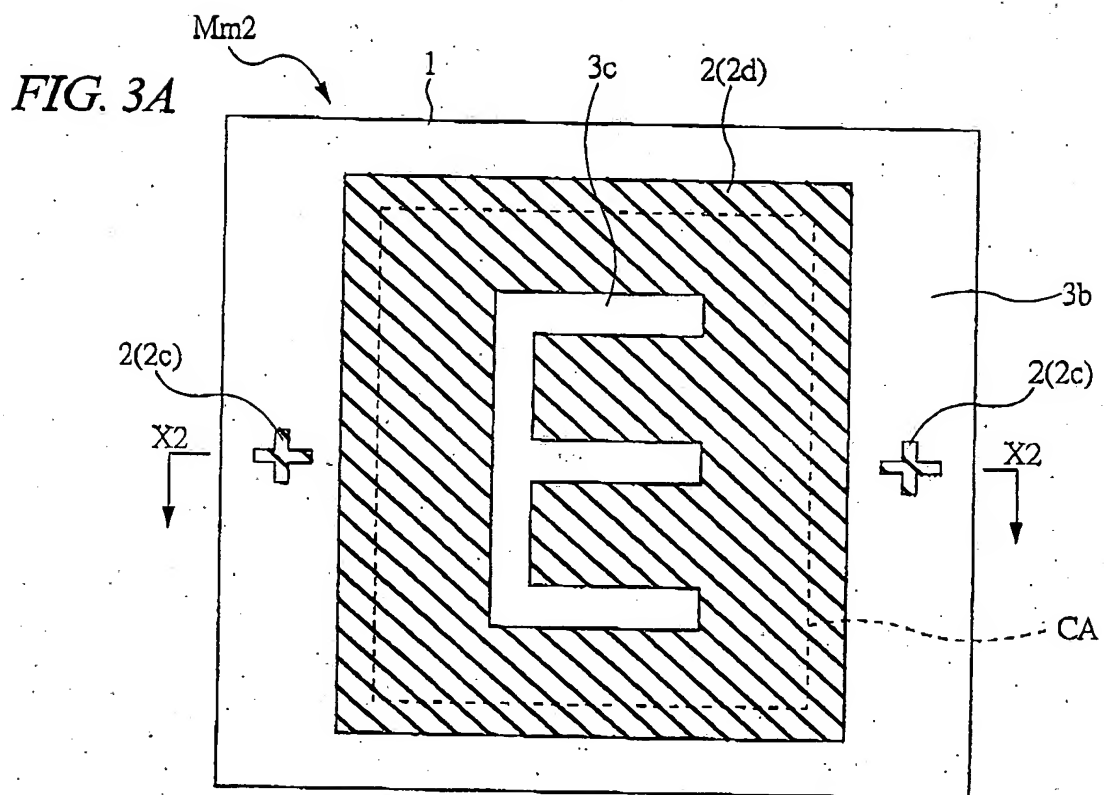
207: Product partial resist mask is completed.

FIG. 1

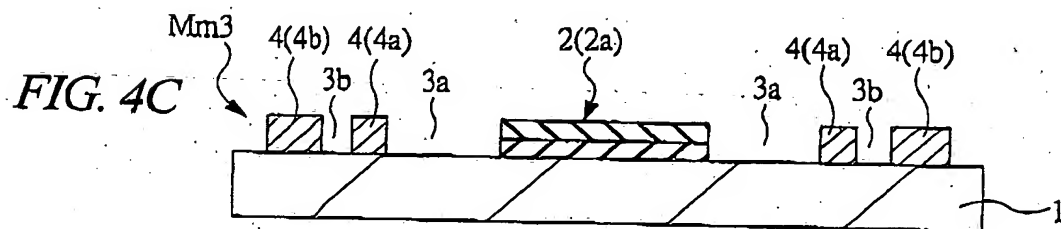
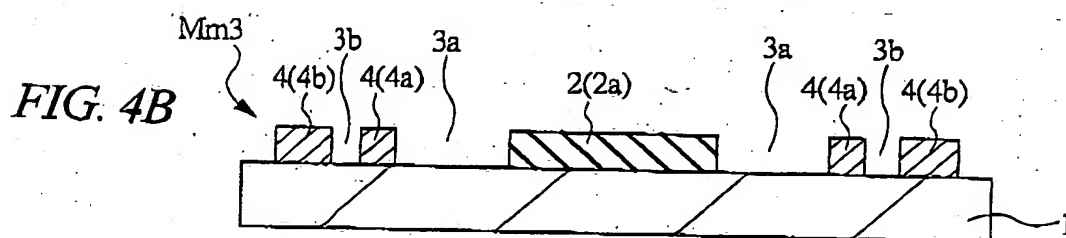
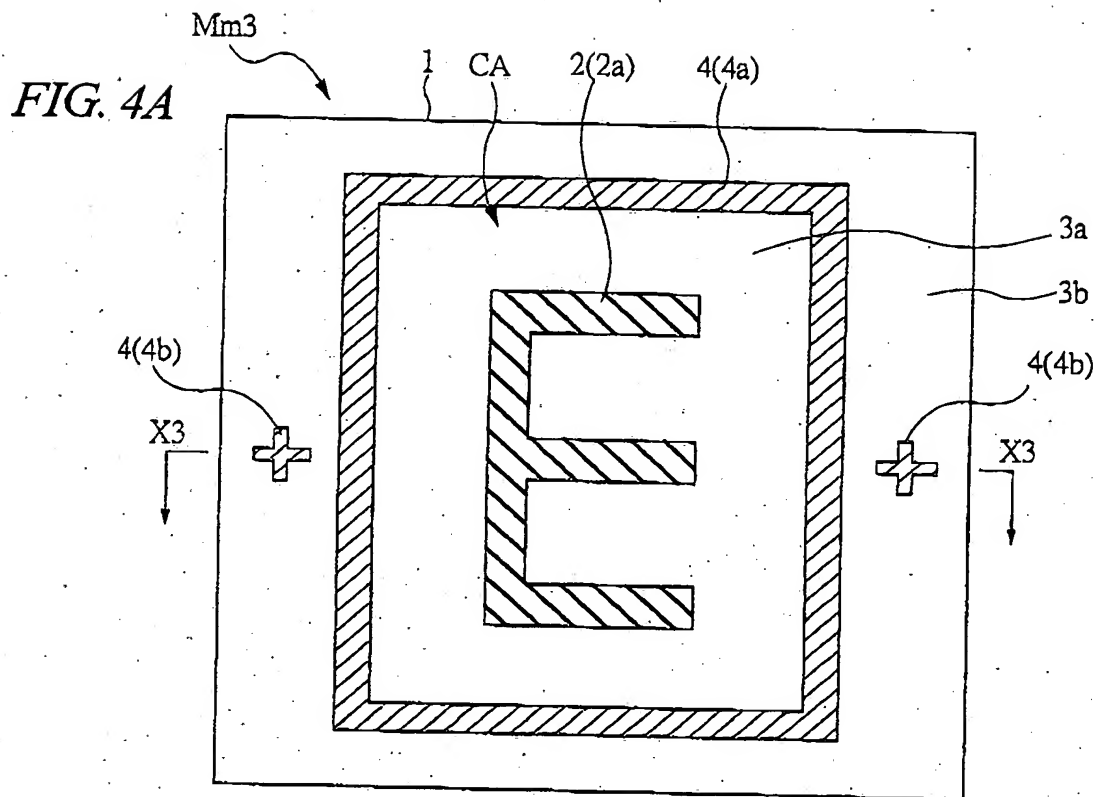


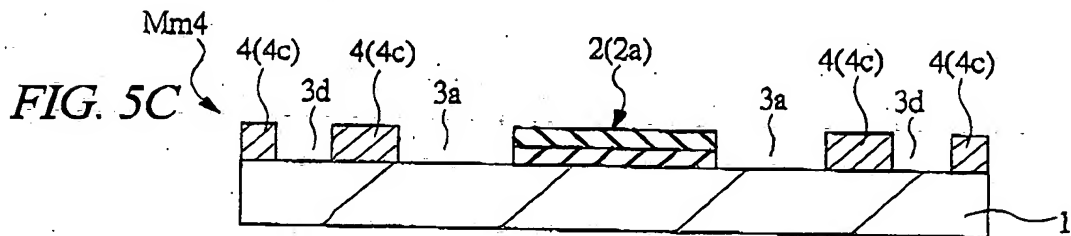
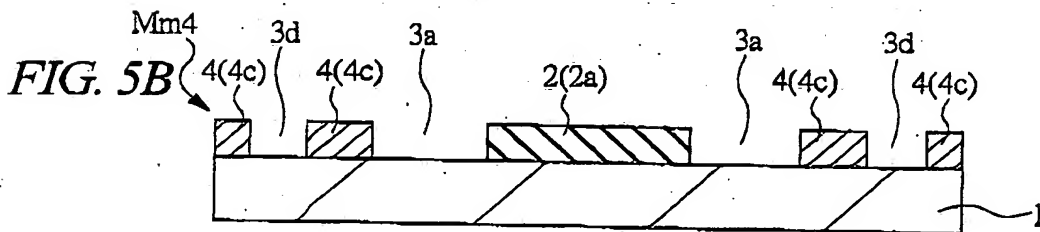
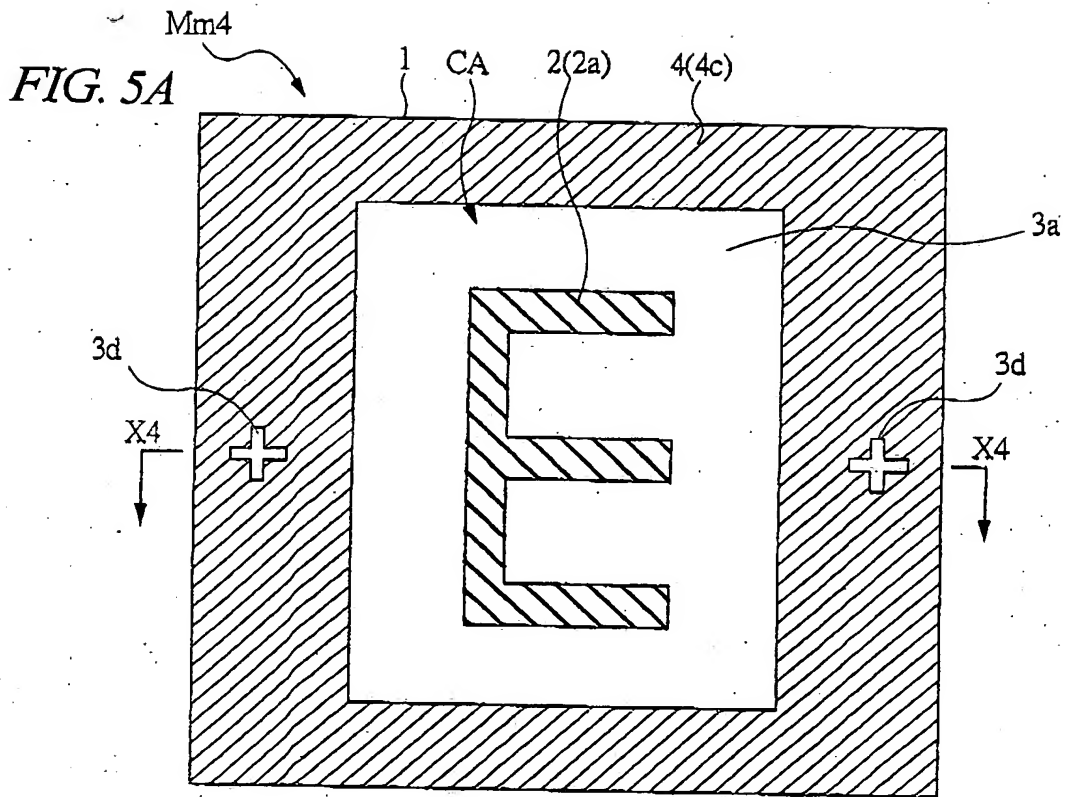


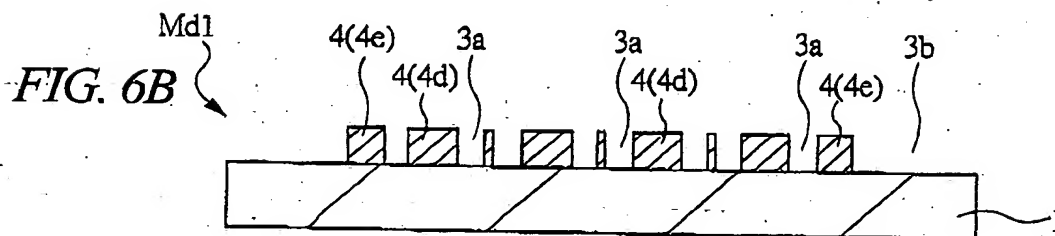
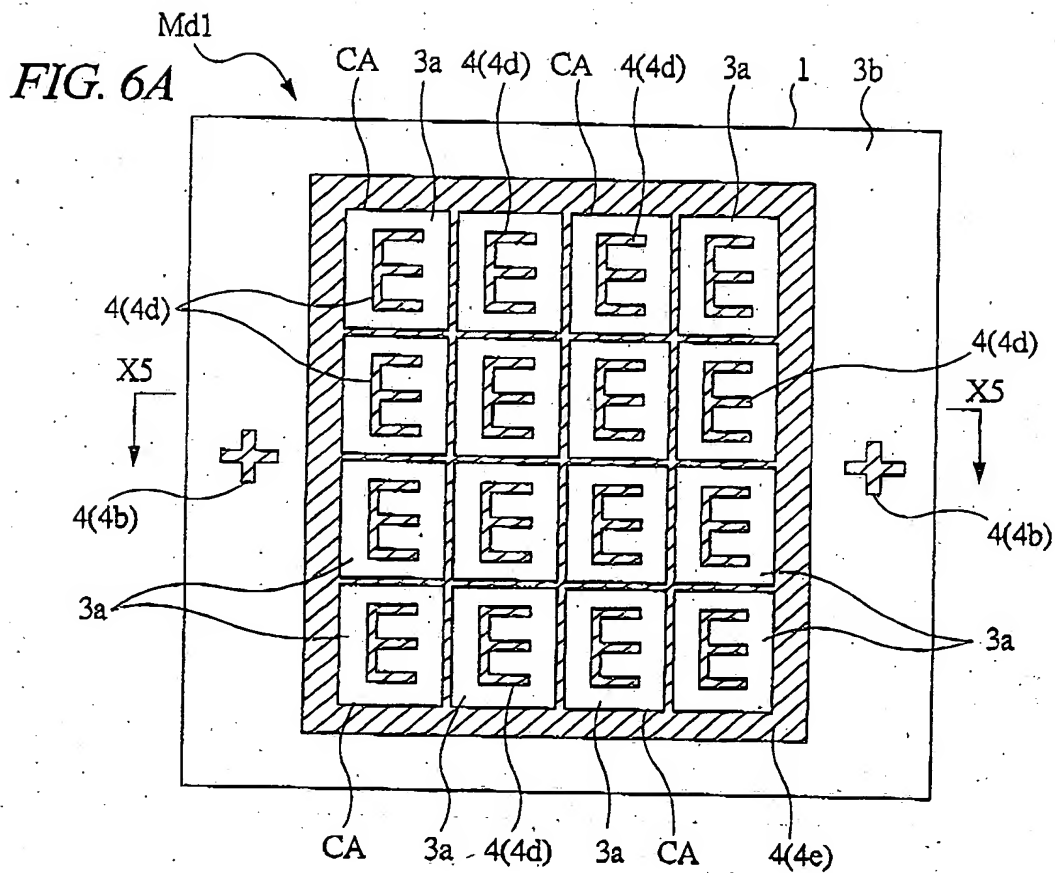
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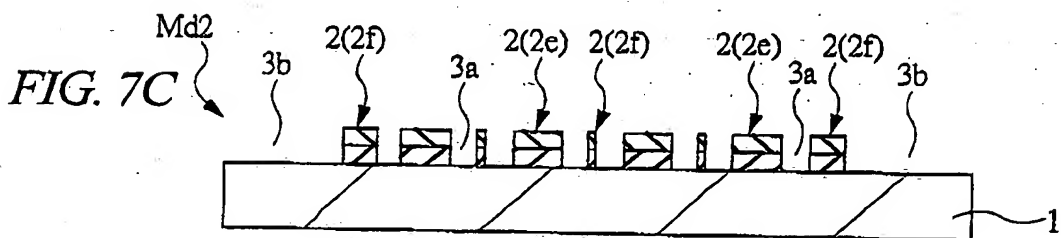
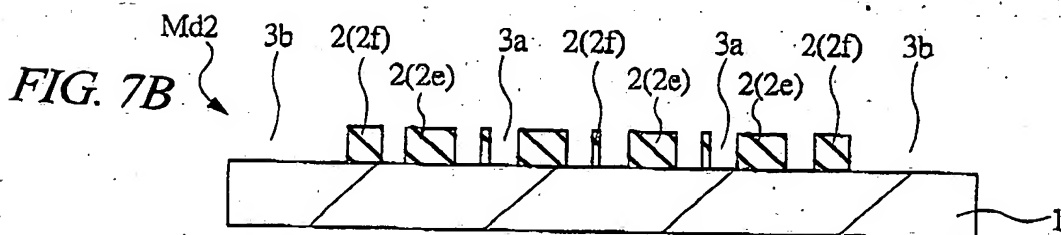
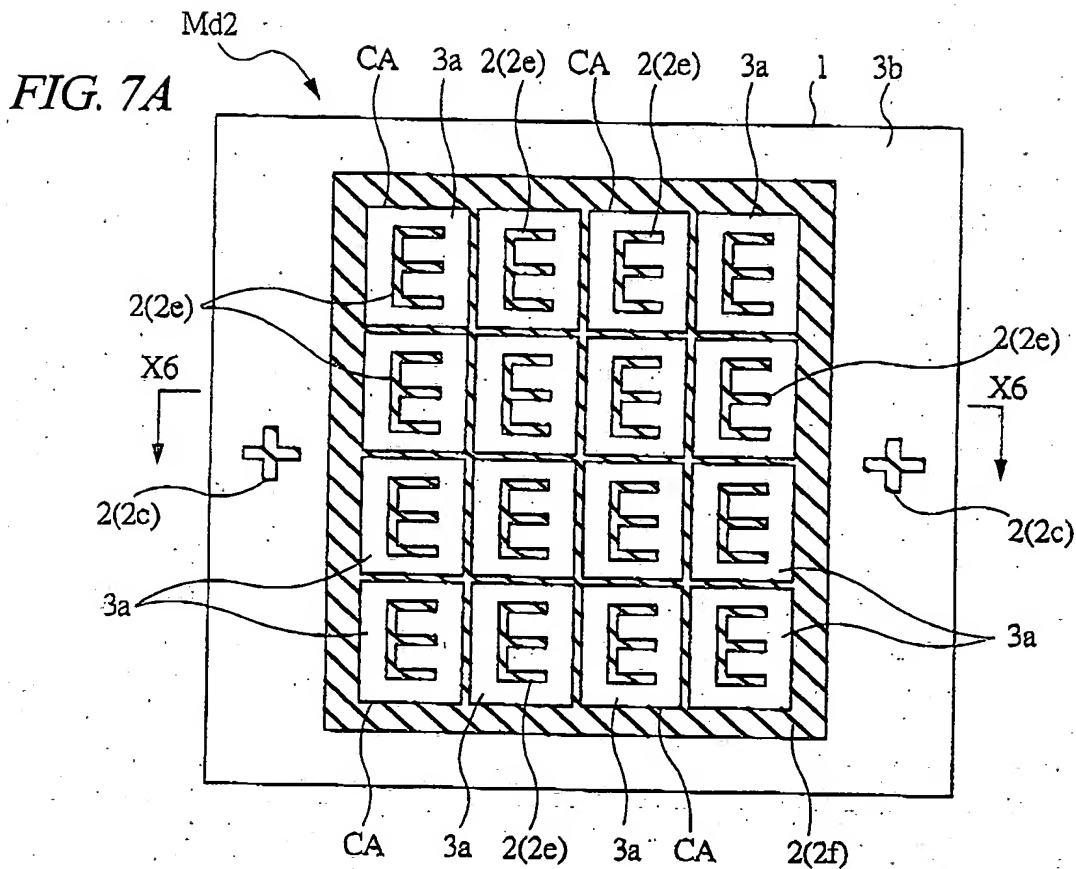


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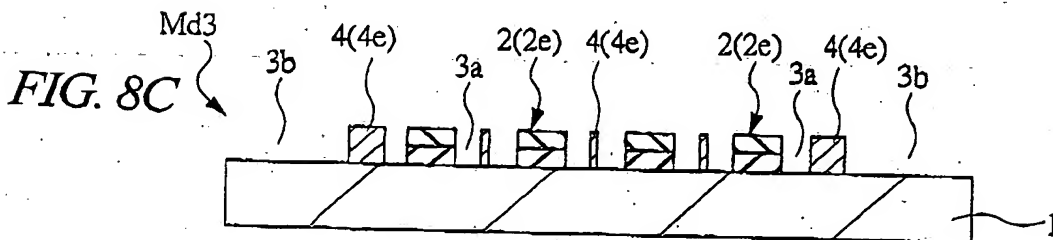
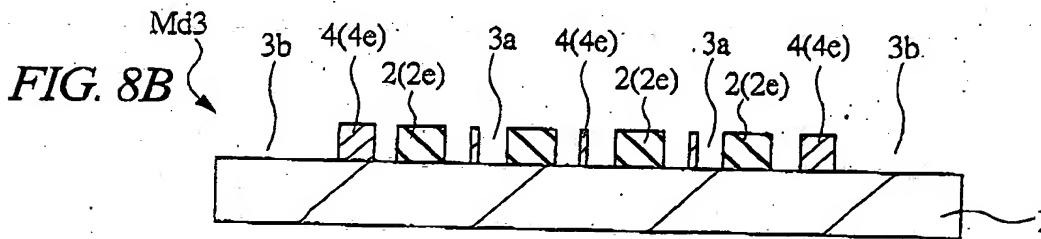
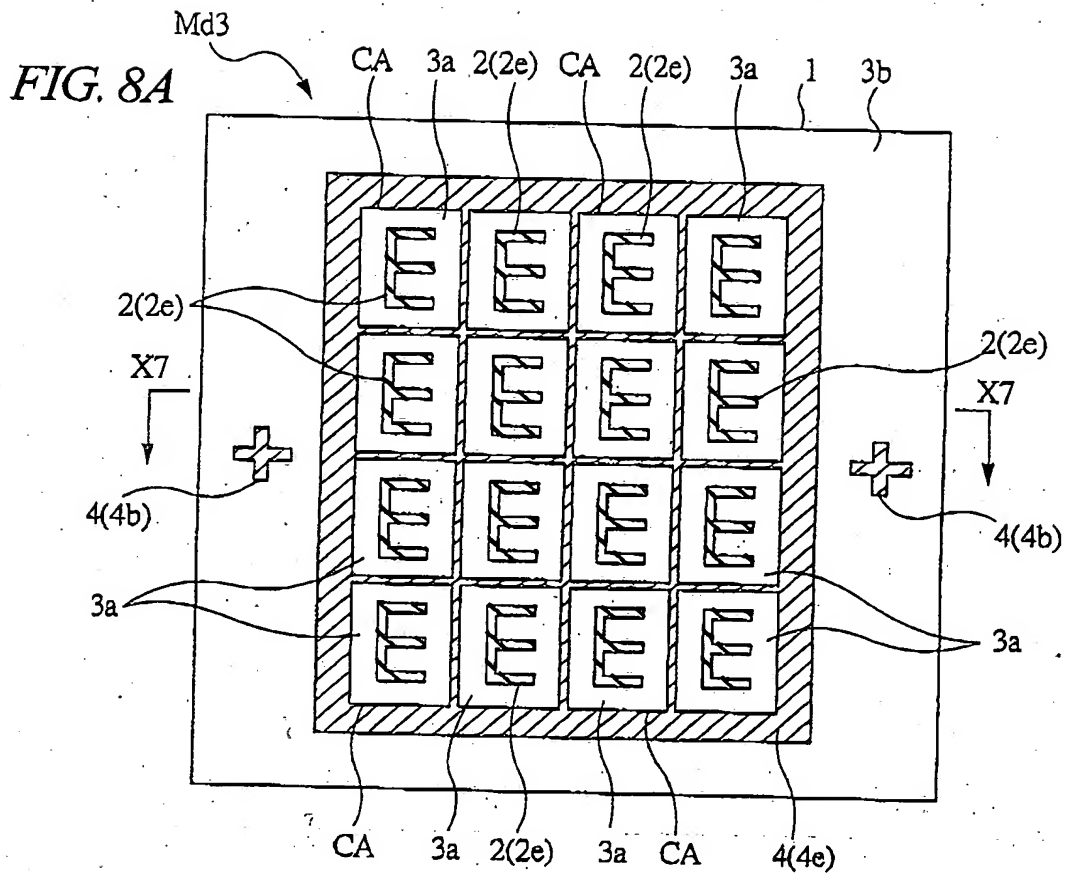


FIG. 9A

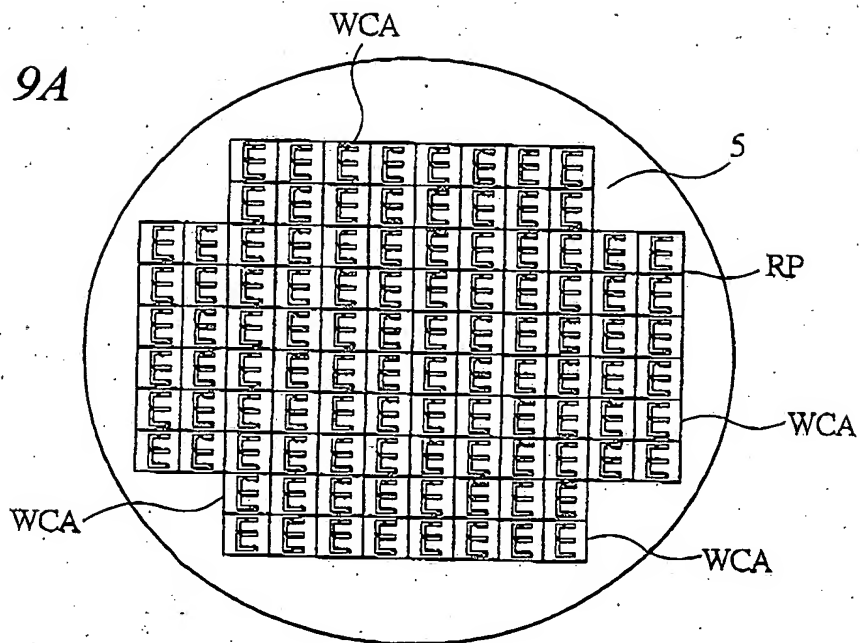


FIG. 9B

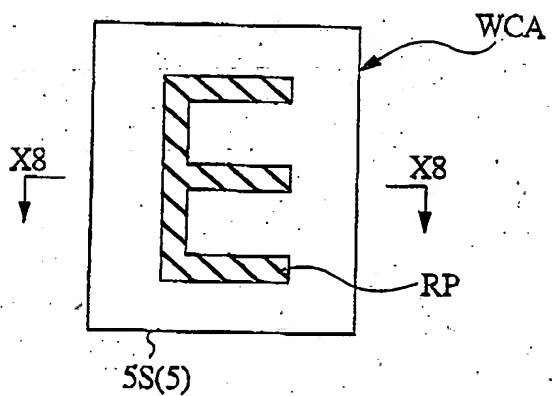


FIG. 9C

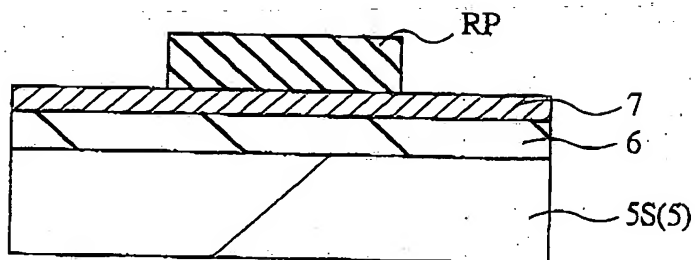


FIG. 10

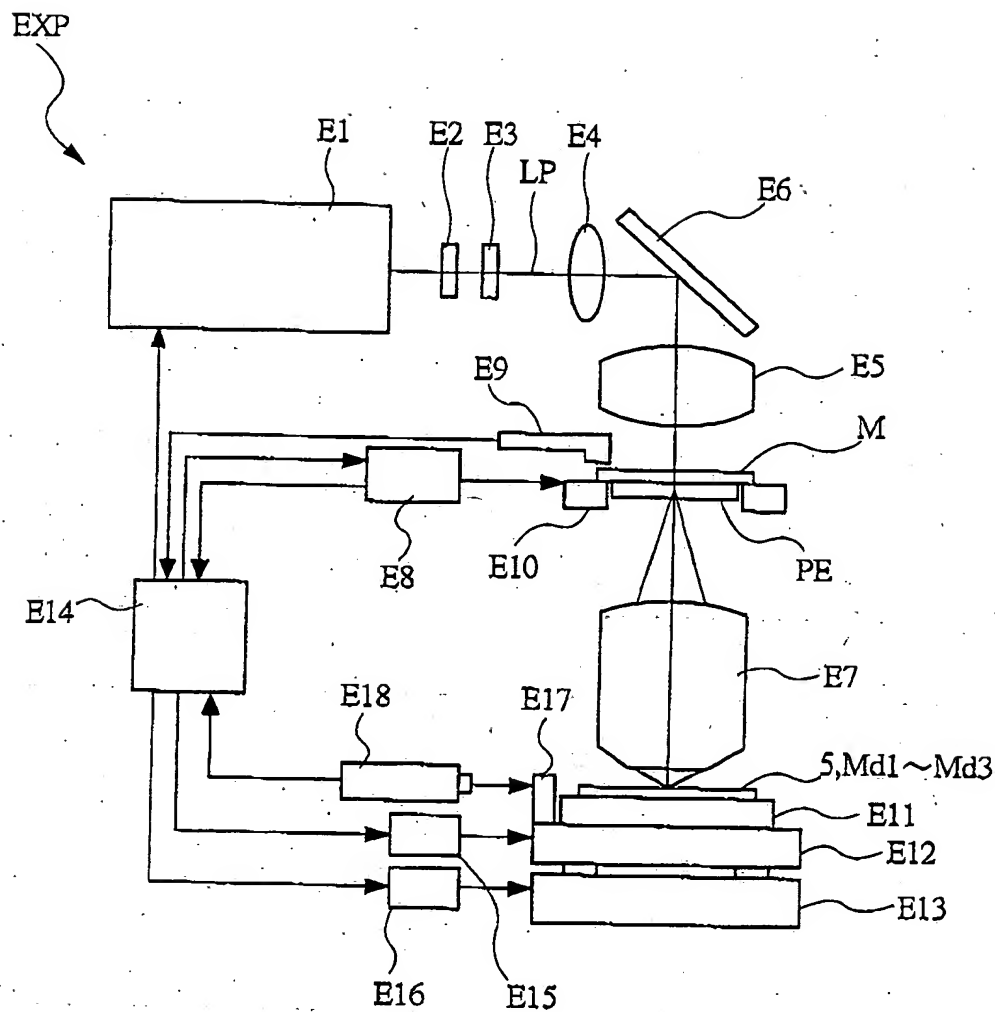
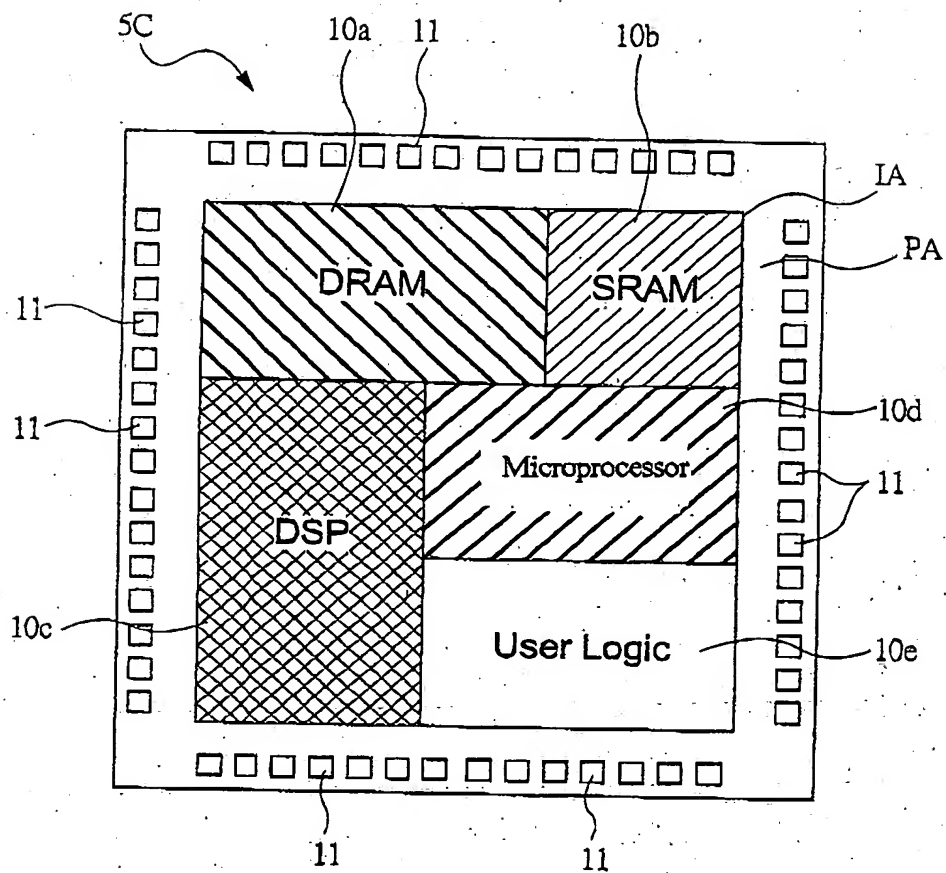


FIG. 11



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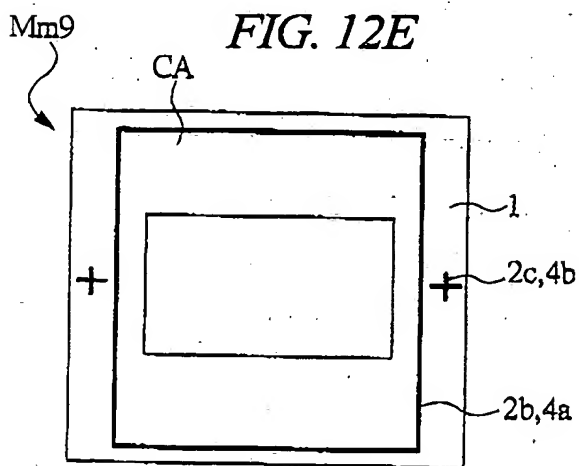
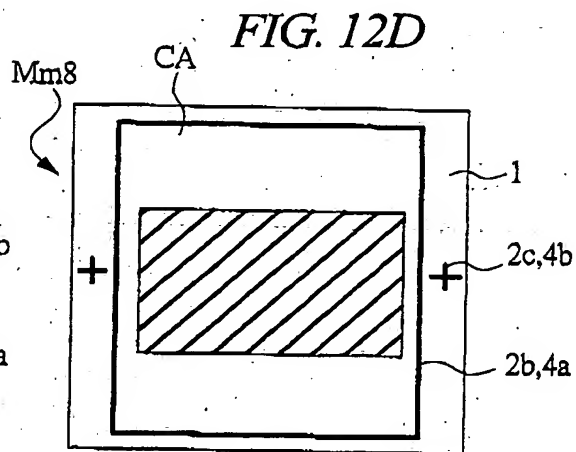
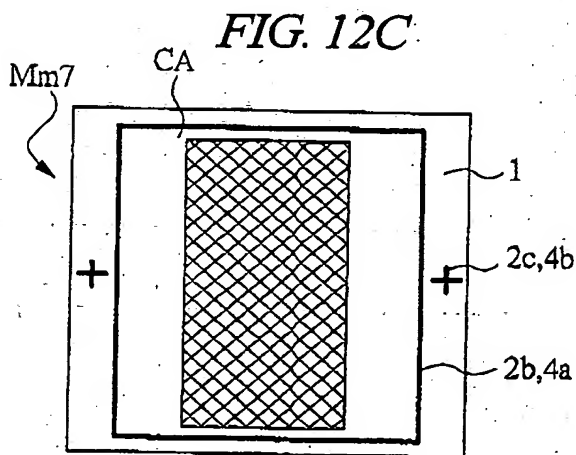
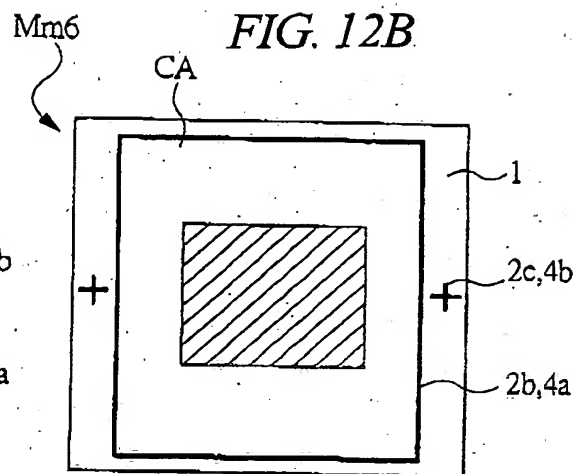
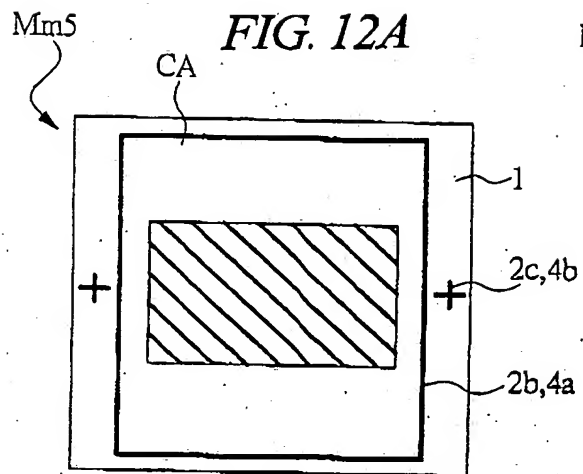


FIG. 13

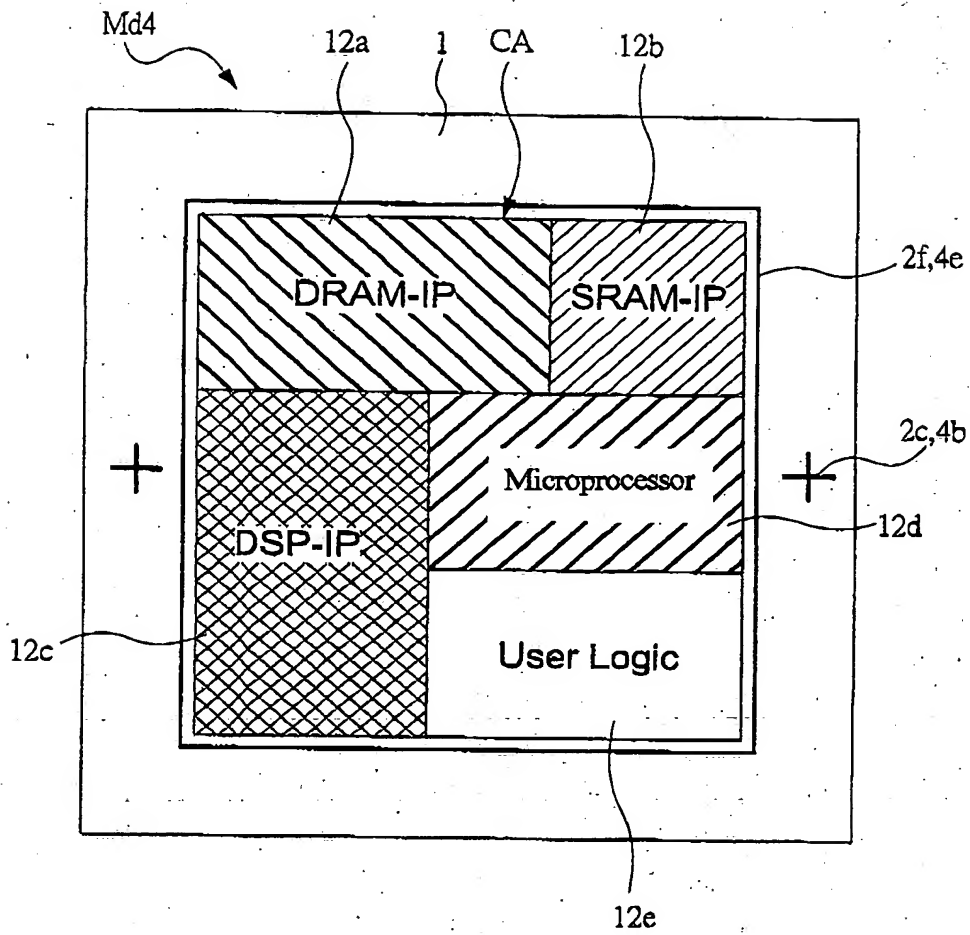
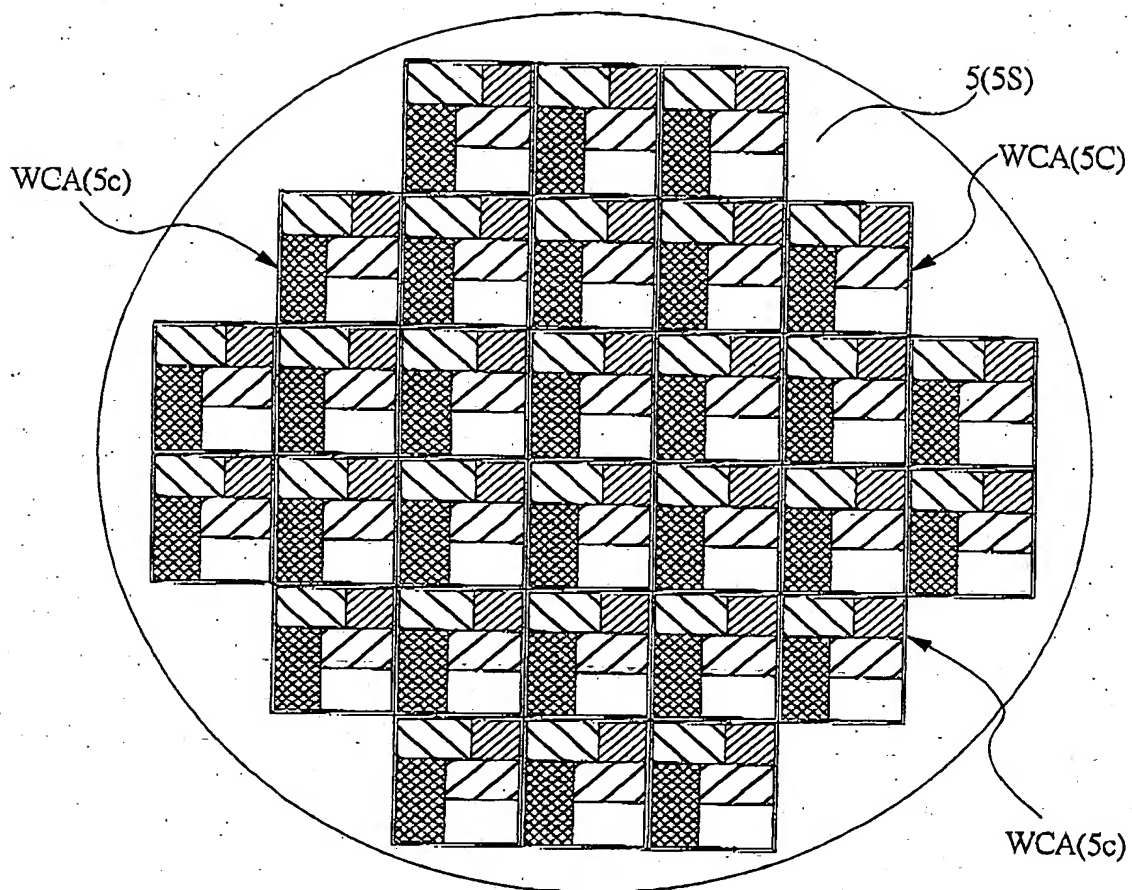
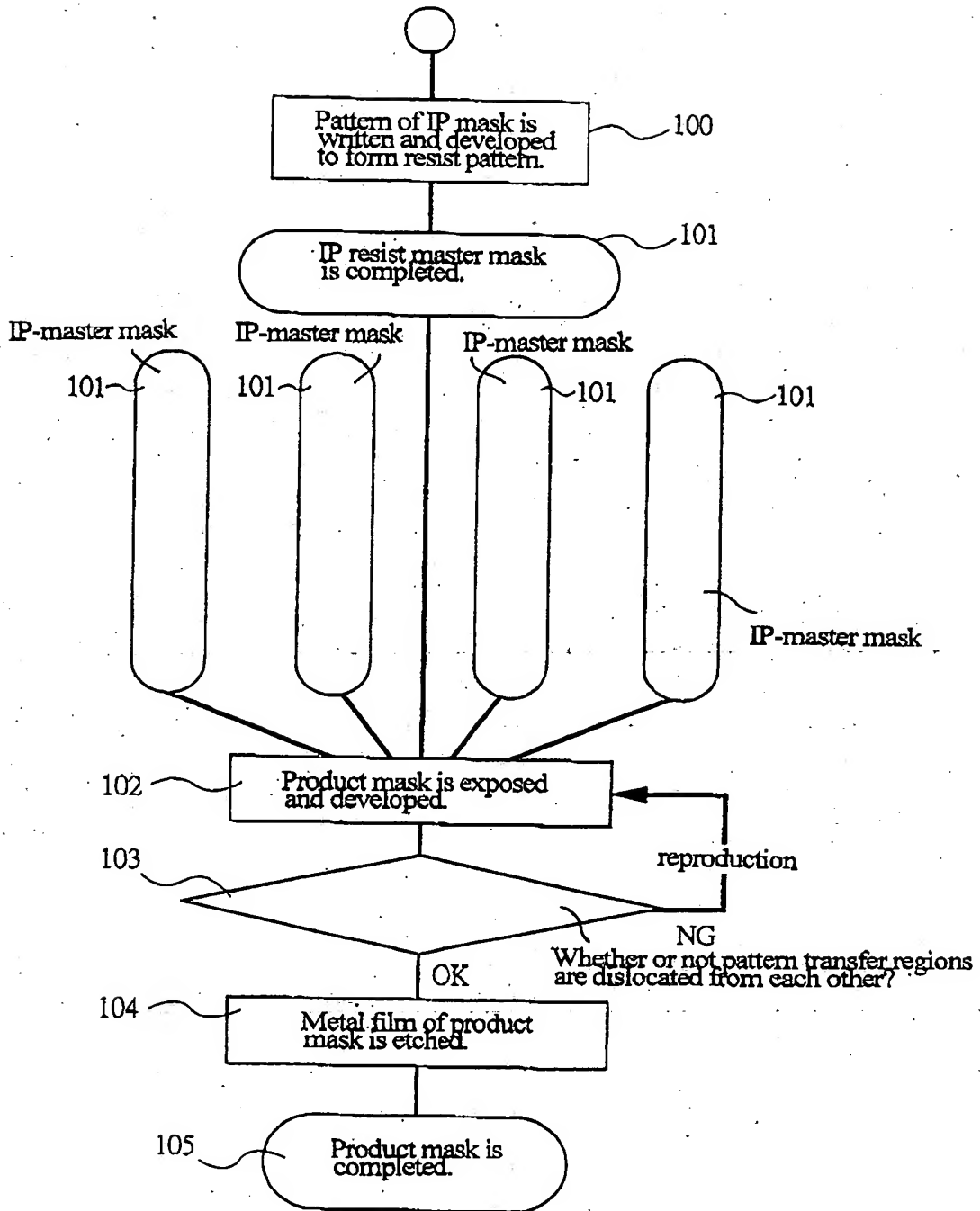


FIG. 14



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FIG. 15



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FIG. 16A

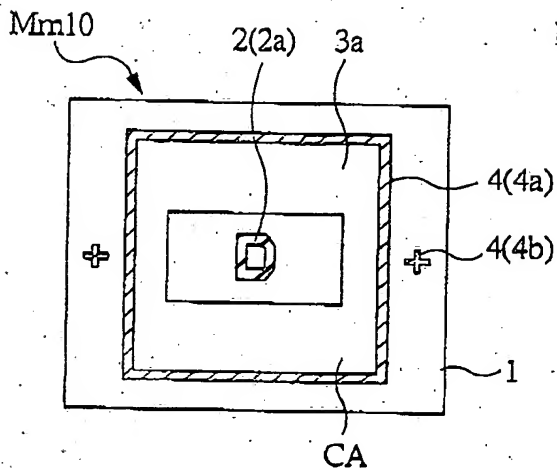


FIG. 16B

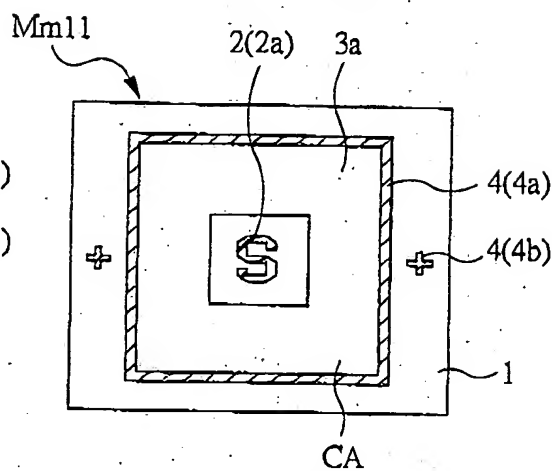


FIG. 16C

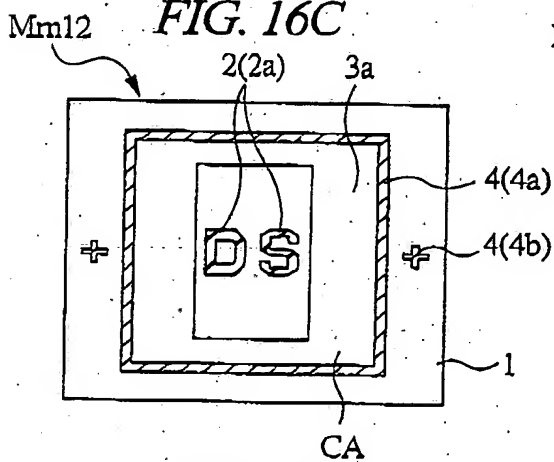


FIG. 16D

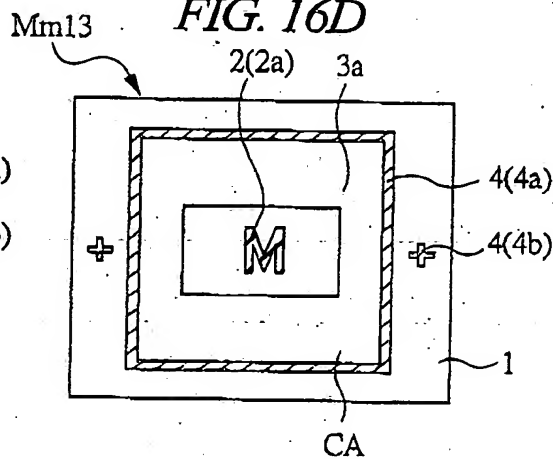


FIG. 16E

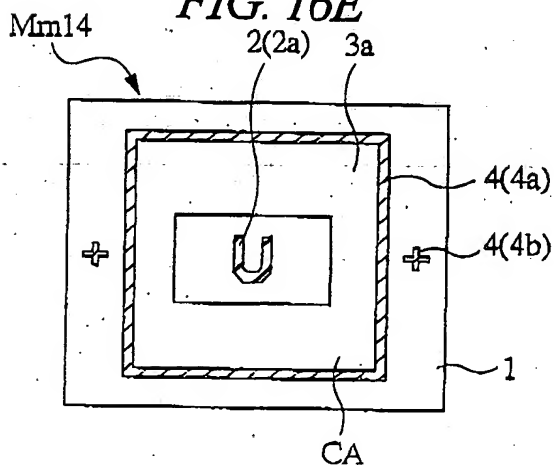
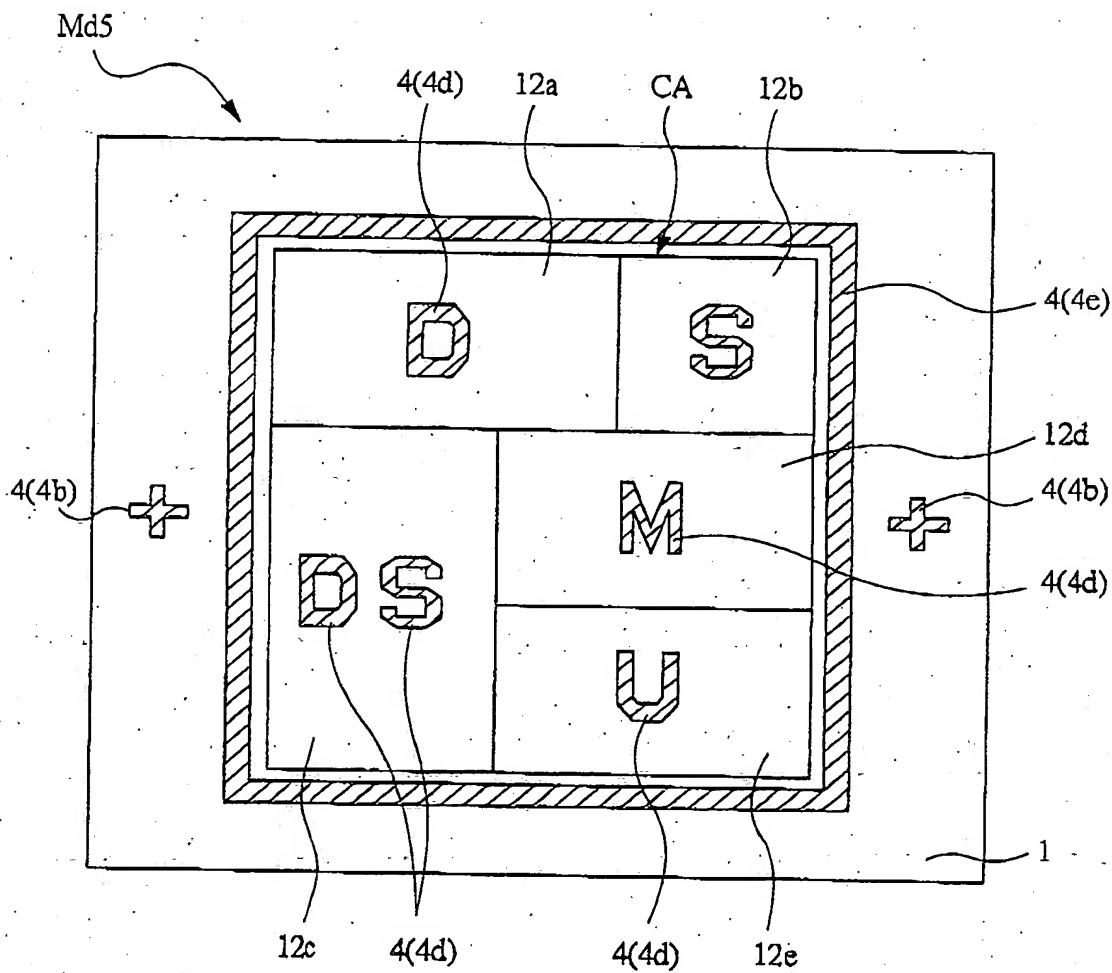


FIG.17



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FIG. 18

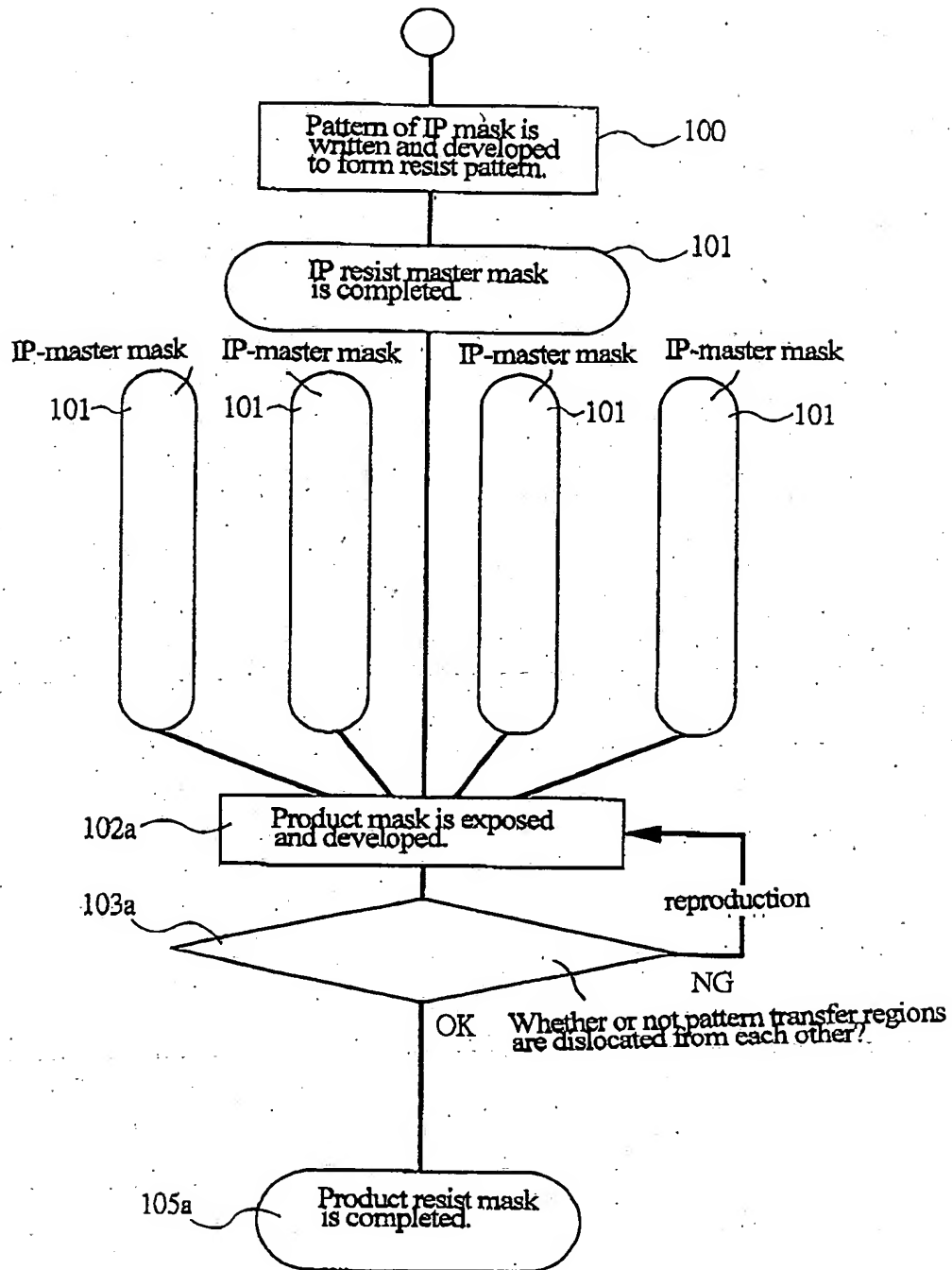


FIG. 18

FIG. 20

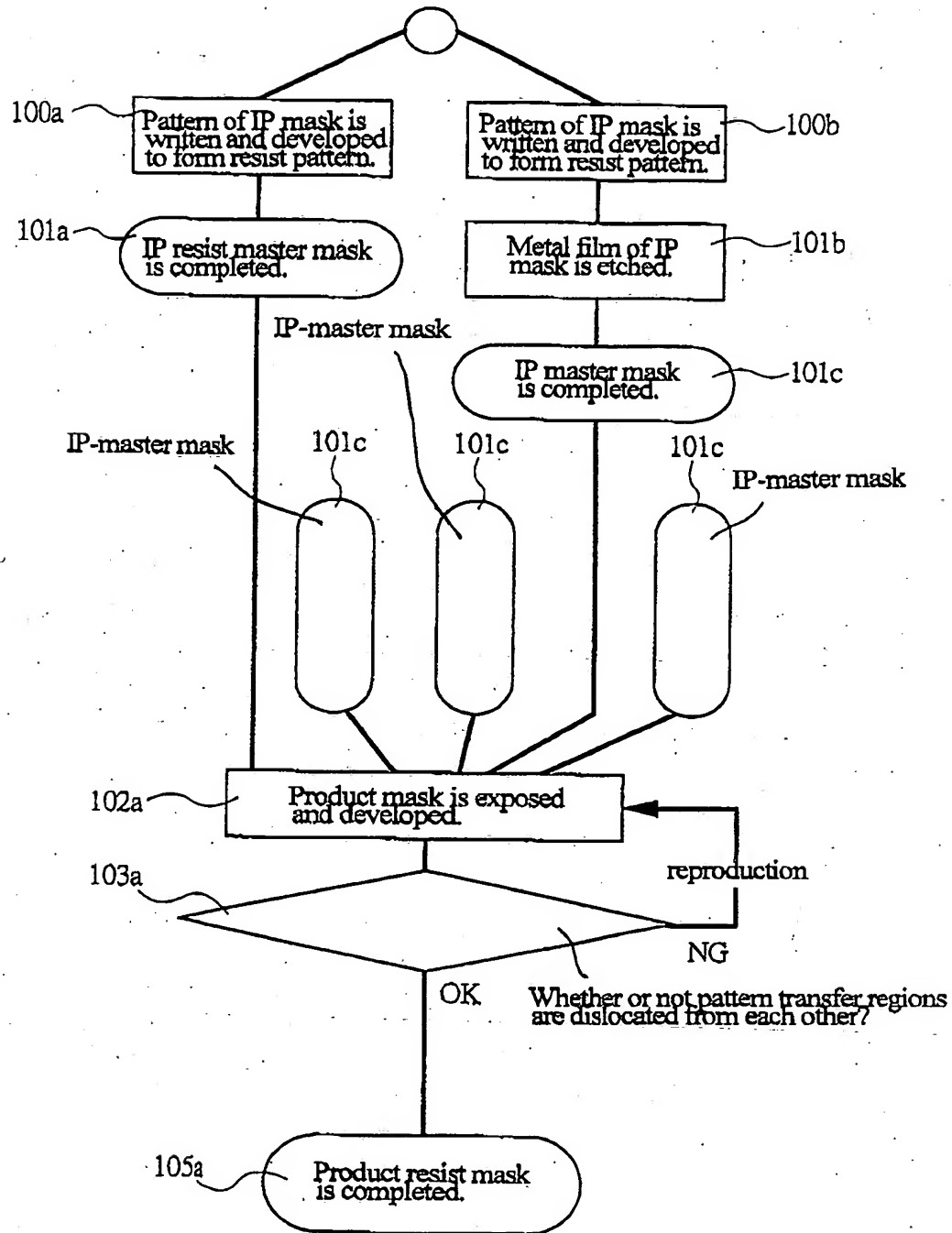


FIG. 20

FIG. 21A

FIG. 21A

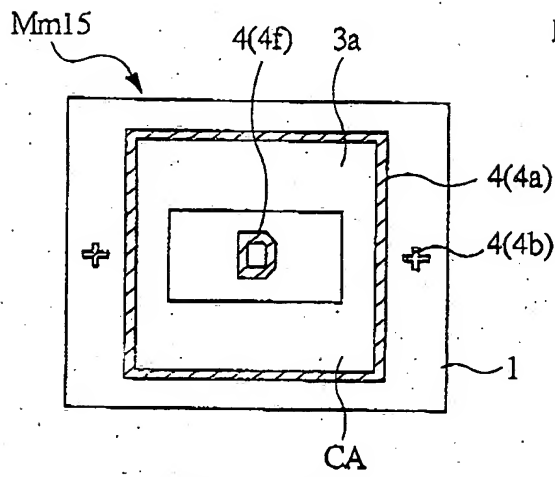


FIG. 21B

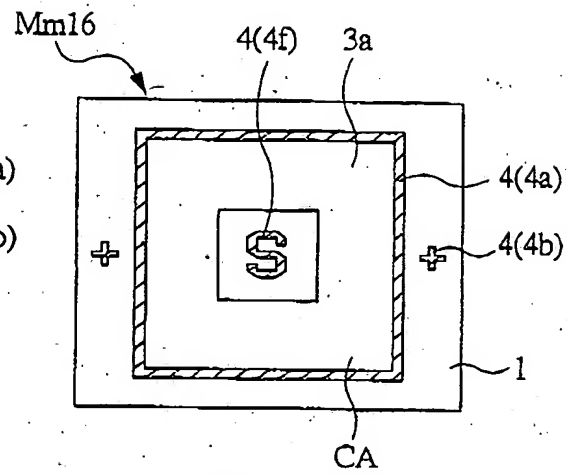


FIG. 21C

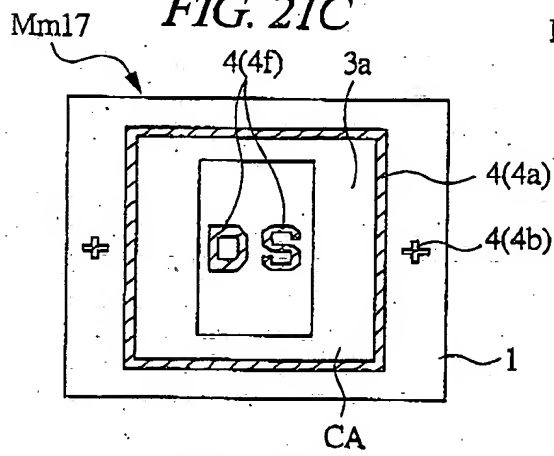


FIG. 21D

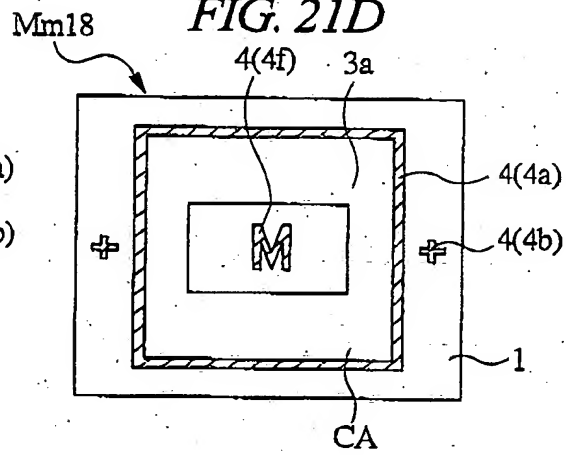


FIG. 21E

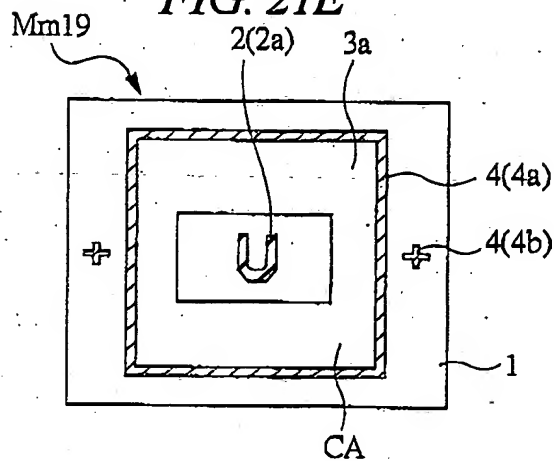


FIG. 22A

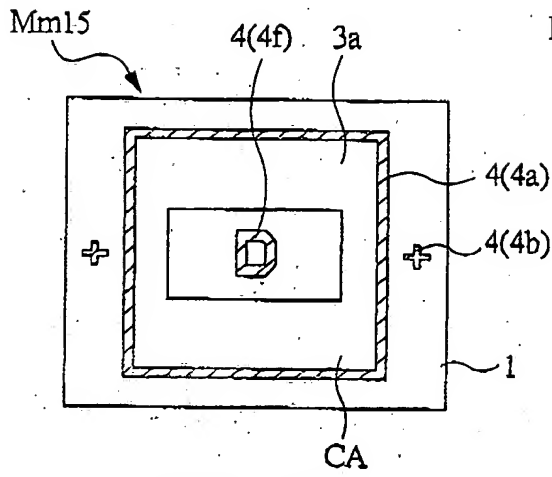


FIG. 22B

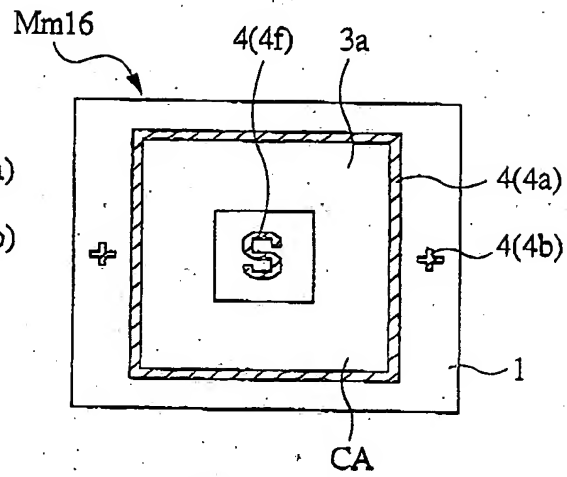


FIG. 22C

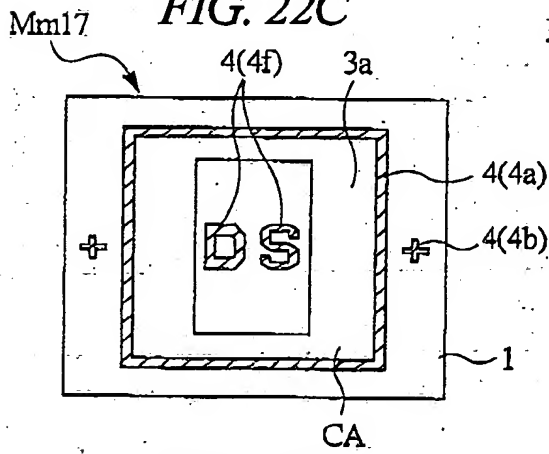


FIG. 22D

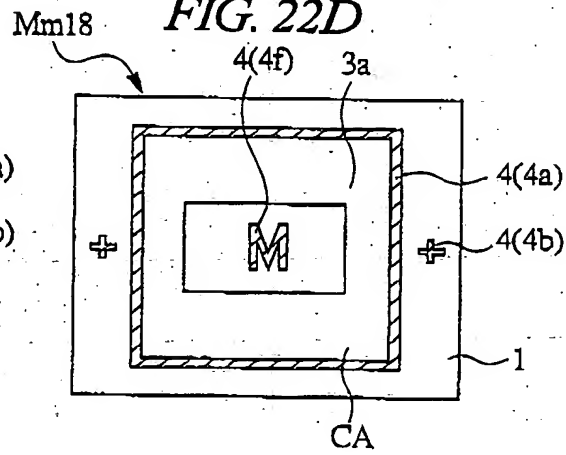


FIG. 22E

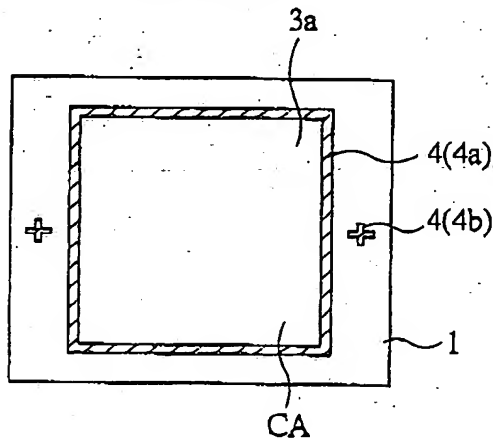


FIG. 23A

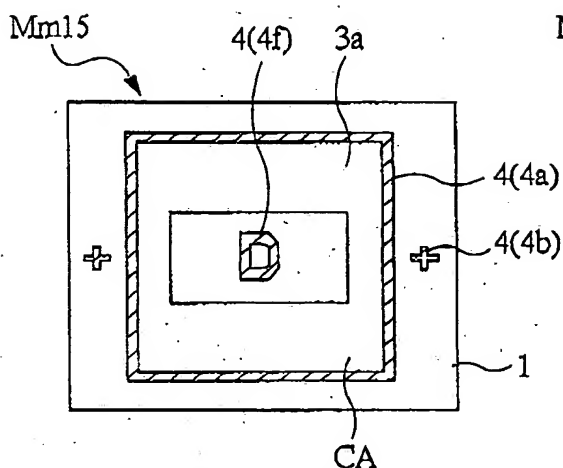


FIG. 23B

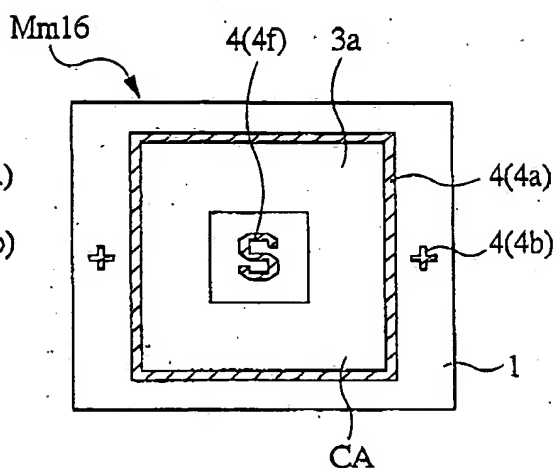


FIG. 23C

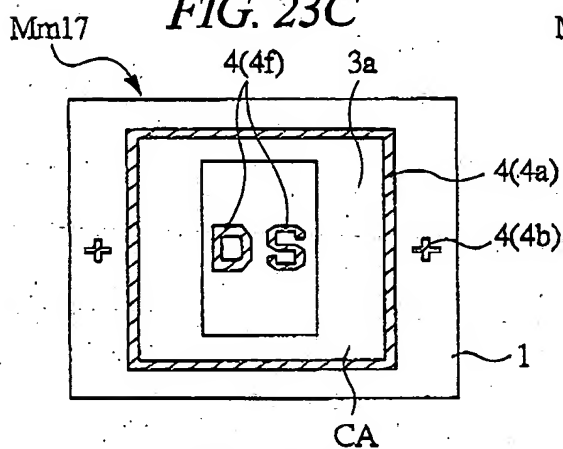


FIG. 23D

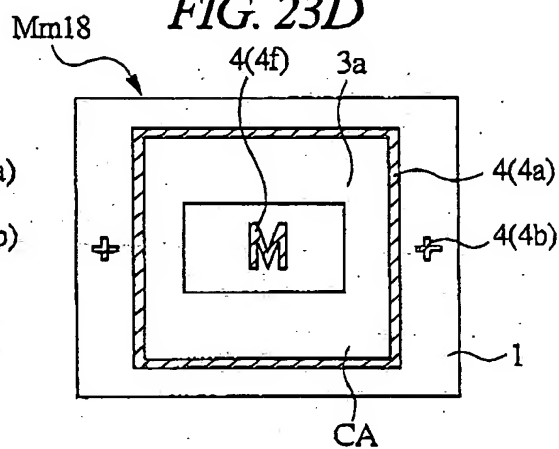


FIG. 23E

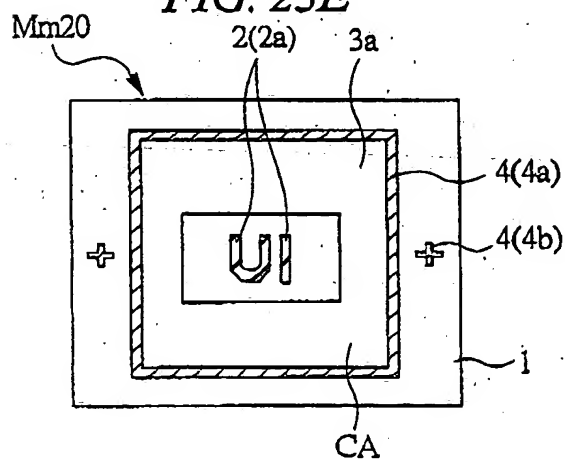


FIG. 24

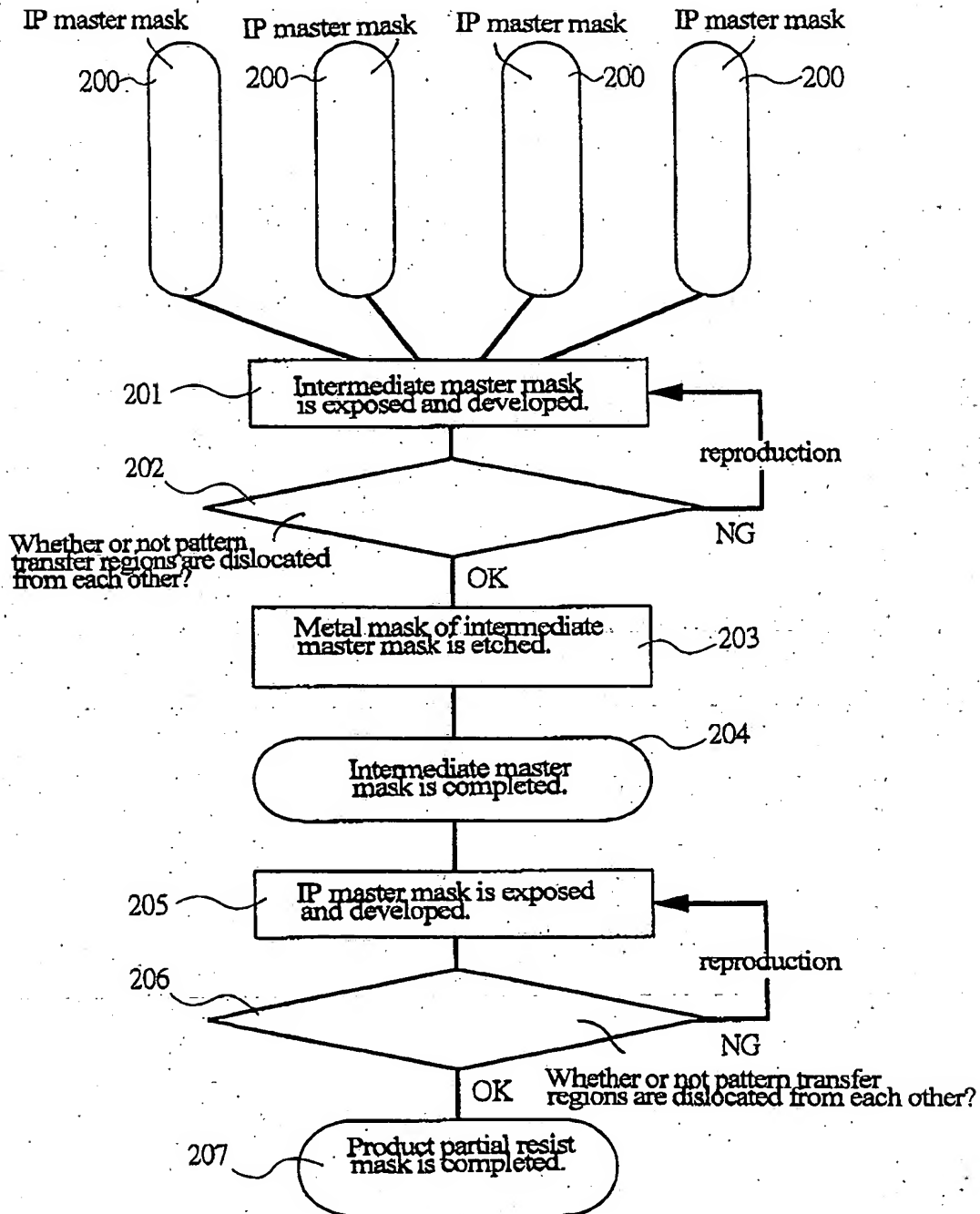
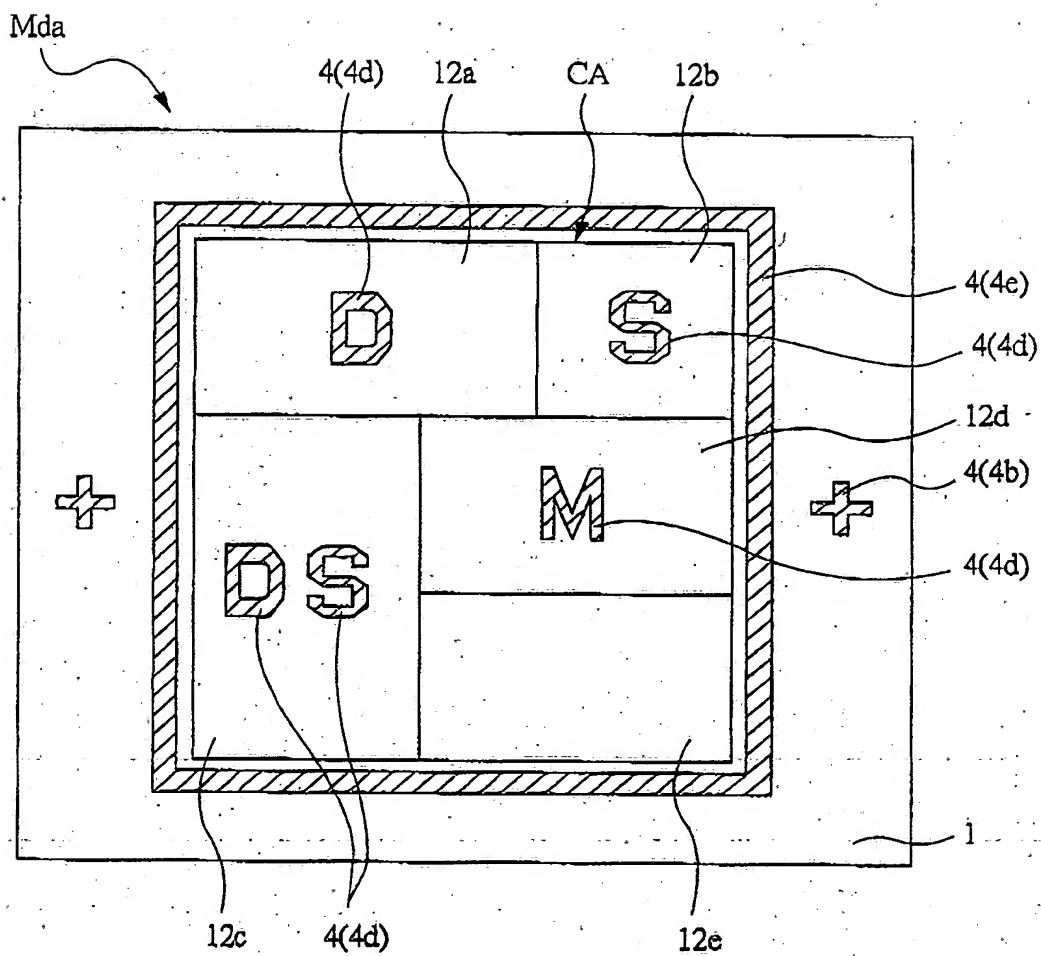
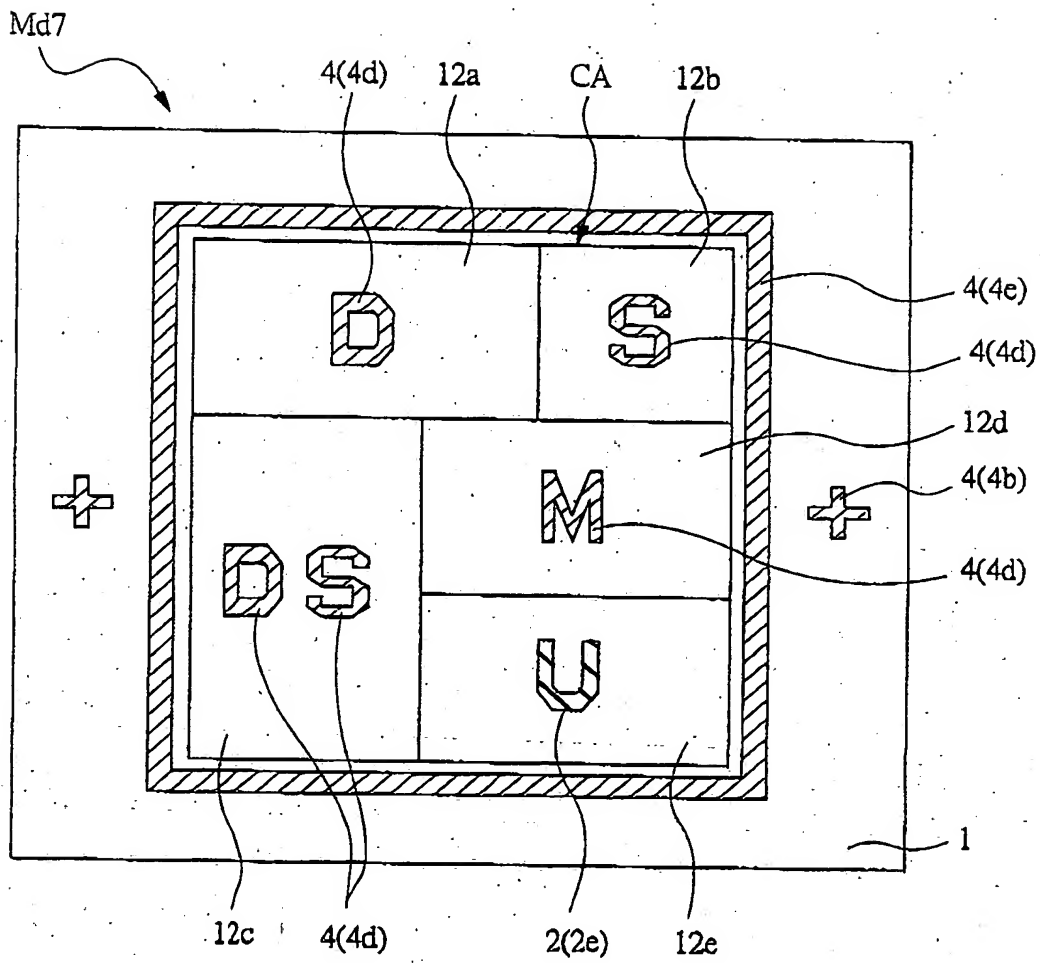


FIG. 25



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FIG. 26



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FIG. 27

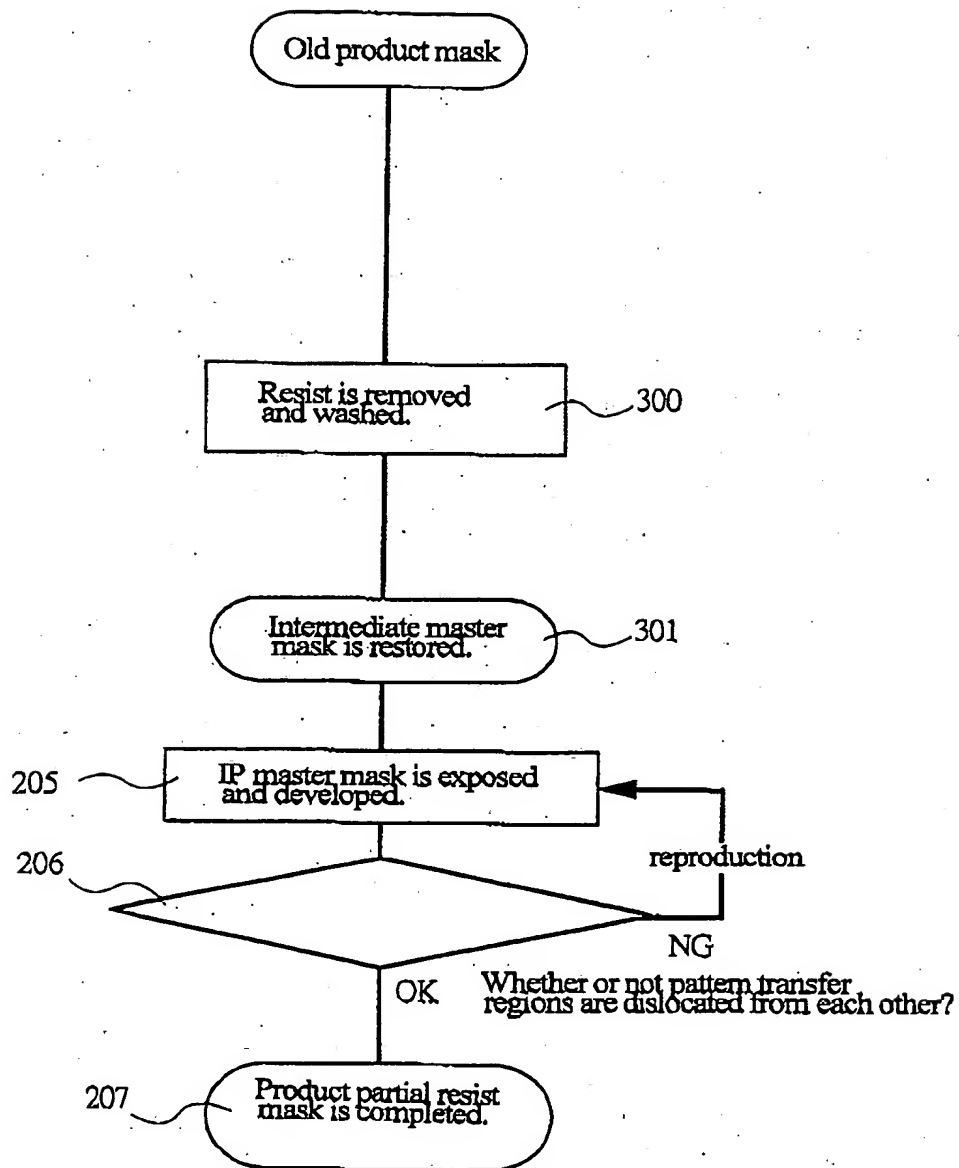
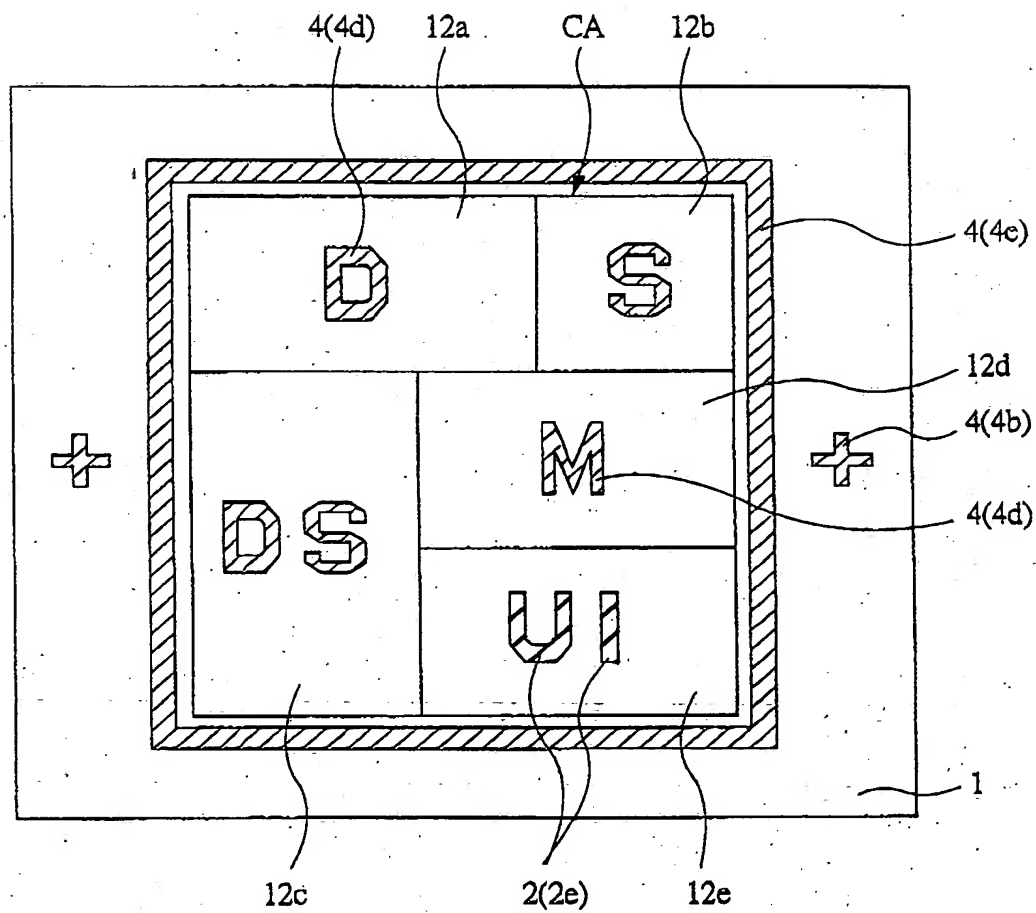


FIG. 28



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FIG. 30A

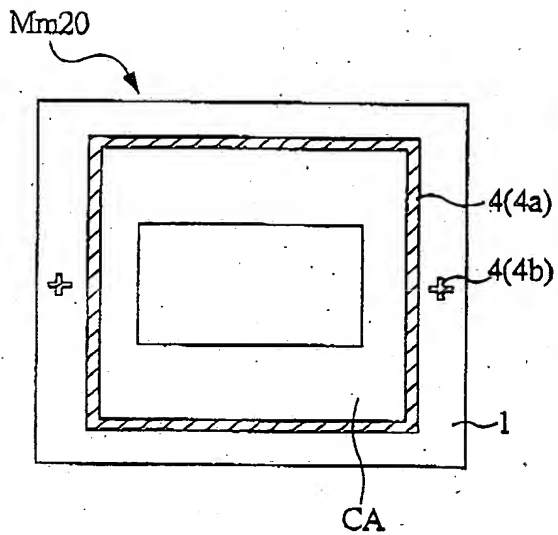


FIG. 30B

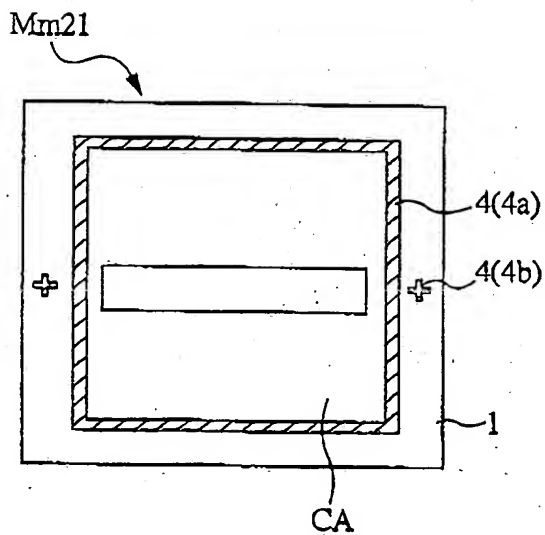


FIG. 30C

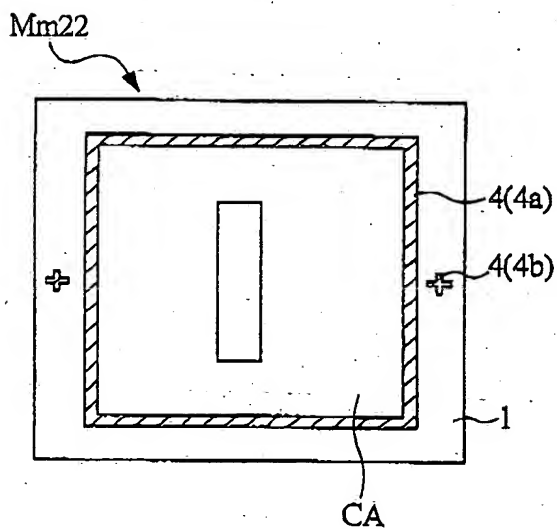
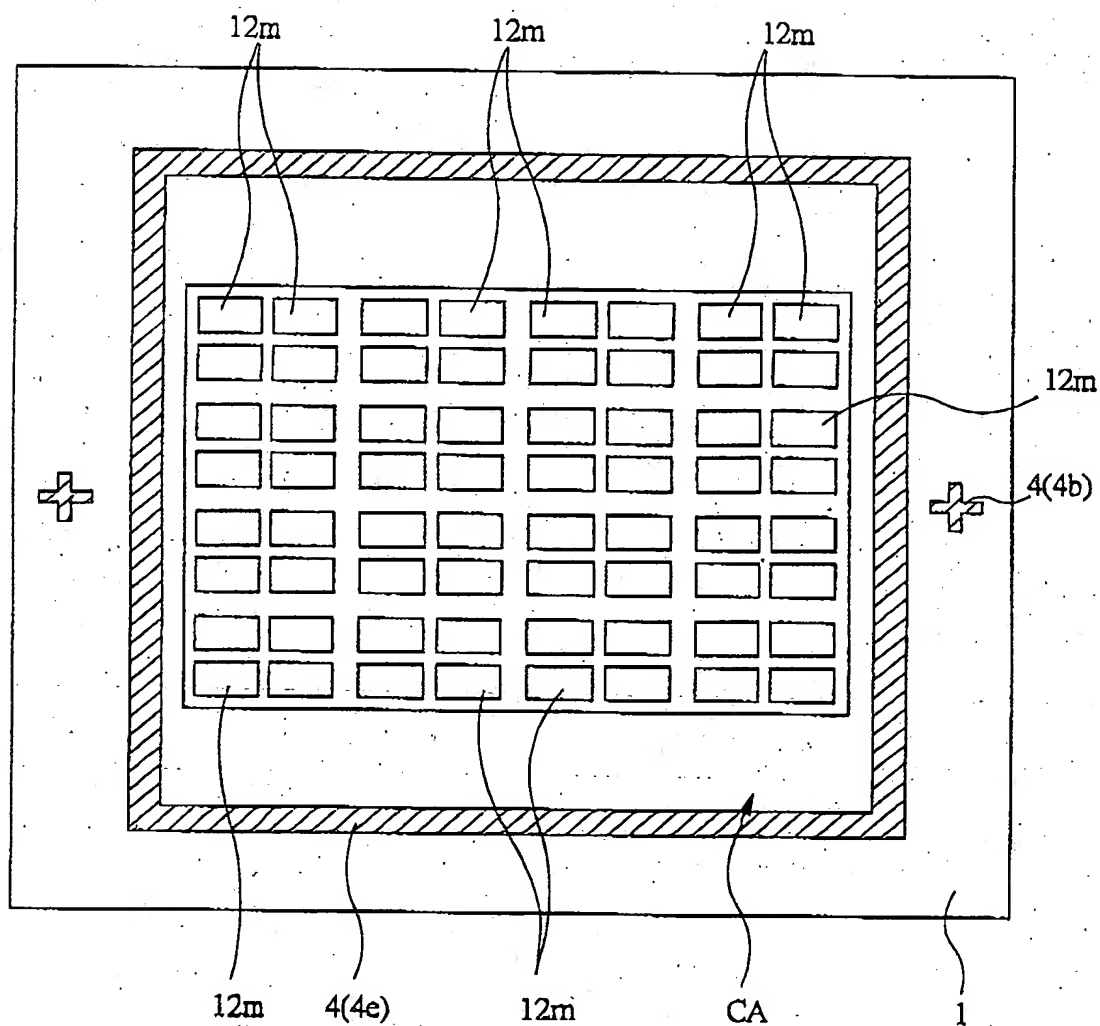


FIG. 31



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FIG. 32

